

INFRARED EMITTING DIODE

Model No. LN-1A11T

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward current	I _F	40	mA
Pulse forward current	I _{FP}	1	A
Reverse voltage	V _R	5	V
Operating temperature	T _{opr}	-20 to +70	°C
Storage temperature	T _{stg}	-25 to +80	°C
Power dissipation	P _M	75	mW
<i>Lead soldering temperature (5mm from body) 260°C for 5 sec.</i>			

ELECTRICAL OPTICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	CONDITION	Min.	Typ.	Max.	UNIT
Forward voltage	V _F	I _F =20mA		1.3	1.5	V
Reverse current	I _R	V _R =5V			10	uA
Peak emission wavelength	λ_p	I _F =20mA		940		nm
Spectral band width	$\Delta \lambda$	I _F =20mA		50		nm
Breakdown voltage	V _{BR}	I _R =100uA	5	30		V
Switching time <i>t_e</i> from 10% to 90%	T _r /T _f	I _F =20mA		700/500		ns
Viewing half angle	$2\theta_{1/2}$	I _F =20mA		70		deg.
Power output	P _o	I _F =20mA		2.0		mW/cm

Unit : mm

